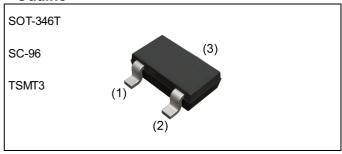
#### Nch 30V 4A Middle Power MOSFET

| V <sub>DSS</sub>           | 30V   |
|----------------------------|-------|
| R <sub>DS(on)</sub> (Max.) | 48mΩ  |
| I <sub>D</sub>             | ±4.0A |
| P <sub>D</sub>             | 1.0W  |

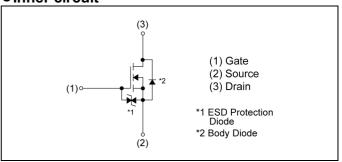
# ●Features

- 1) Low on resistance.
- 2) Built-in G-S Protection Diode.
- 3) Small Surface Mount Package (TSMT3).

### Outline



#### ●Inner circuit



Packaging specifications

|      | Packing                   | Embossed<br>Tape |
|------|---------------------------|------------------|
|      | Reel size (mm)            | 180              |
| Туре | Tape width (mm)           | 8                |
|      | Basic ordering unit (pcs) | 3000             |
|      | Taping code               | TL               |
|      | Marking                   | QV               |

## Application

Switching

#### ● **Absolute maximum ratings** (T<sub>a</sub> = 25°C ,unless otherwise specified)

| Parameter  | Symbol             | Value       | Unit |
|--|--------------------|-------------|------|
| Drain - Source voltage                           | V <sub>DSS</sub>   | 30          | V    |
| Continuous drain current                         | I <sub>D</sub>     | ±4.0        | Α    |
| Pulsed drain current                             | I <sub>DP</sub> *1 | ±16         | Α    |
| Gate - Source voltage                            | V <sub>GSS</sub>   | ±12         | V    |
| Douge dissinction                                | P <sub>D</sub> *2  | 1.0         | W    |
| Power dissipation                                | P <sub>D</sub> *3  | 0.76        | W    |
| Junction temperature                             | T <sub>j</sub>     | 150         | °C   |
| Operating junction and storage temperature range | T <sub>stg</sub>   | -55 to +150 | °C   |

#### ●Thermal resistance

| Parameter                              | Symbol               | Values |      |      | Linit |
|--|----------------------|--------|------|------|-------|
| raianietei                             | Symbol               | Min.   | Тур. | Max. | Unit  |
| Thermal registance innetion, ambient   | R <sub>thJA</sub> *2 | -      | -    | 125  | °C/W  |
| Thermal resistance, junction - ambient | R <sub>thJA</sub> *3 | -      | -    | 165  | °C/W  |

### ● Electrical characteristics (T<sub>a</sub> = 25°C)

| Darameter                                      | Symbol                                    | Conditions                                    | Values |      | Unit |       |
|--|---|---|--------|------|------|-------|
| Parameter                                      | Parameter Symbol Conditions               |   | Min.   | Тур. | Max. | Offic |
| Drain - Source breakdown<br>voltage            | V <sub>(BR)DSS</sub>                      | V <sub>GS</sub> = 0V, I <sub>D</sub> = 1mA    | 30     | -    | -    | V     |
| Breakdown voltage temperature coefficient      | $\frac{\Delta V_{(BR)DSS}}{\Delta T_{j}}$ | I <sub>D</sub> = 1mA<br>referenced to 25°C    | -      | 29.0 | -    | mV/°C |
| Zero gate voltage drain current                | I <sub>DSS</sub>                          | V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V   | 1      | -    | 1    | μA    |
| Gate - Source leakage current                  | I <sub>GSS</sub>                          | $V_{GS} = 12V, V_{DS} = 0V$                   | 1      | -    | 10   | μA    |
| Gate threshold voltage                         | V <sub>GS(th)</sub>                       | $V_{DS} = 10V$ , $I_D = 1mA$                  | 0.5    | -    | 1.5  | V     |
| Gate threshold voltage temperature coefficient | $\frac{\Delta V_{GS(th)}}{\Delta T_{j}}$  | I <sub>D</sub> = 1mA<br>referenced to 25°C    | -      | -1.6 | -    | mV/°C |
|  |   | V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 4.0A | -      | 34   | 48   |       |
| Static drain - source on - state resistance    | R <sub>DS(on)</sub> *4                    | V <sub>GS</sub> = 4.0V, I <sub>D</sub> = 4.0A | -      | 36   | 50   | mΩ    |
|  |   | V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 4.0A | -      | 47   | 66   |       |
| Gate resistance R <sub>G</sub> f               |   | f = 1MHz, open drain                          | ı      | 6.4  | ı    | Ω     |
| Forward Transfer<br>Admittance                 | Y <sub>fs</sub>  *4                       | $V_{DS} = 10V, I_{D} = 4.0A$                  | 4.0    | -    | -    | S     |

<sup>\*1</sup> Pw  $\leq$  10µs, Duty cycle  $\leq$  1%

<sup>\*2</sup> Mounted on a ceramic board (30×30×0.8mm)

<sup>\*3</sup> Mounted on a FR4 (25×25×0.8mm)

<sup>\*4</sup> Pulsed

## ●Electrical characteristics (T<sub>a</sub> = 25°C)

| Davamatav                    | Curahal                | Conditions                         | Values |      |      | Unit  |  |
|------------------------------|------------------------|------------------------------------|--------|------|------|-------|--|
| Parameter                    | Symbol Conditions      |                                    | Min.   | Тур. | Max. | Uffil |  |
| Input capacitance            | C <sub>iss</sub>       | V <sub>GS</sub> = 0V               | -      | 475  | -    |       |  |
| Output capacitance           | C <sub>oss</sub>       | V <sub>DS</sub> = 10V              | -      | 120  | -    | pF    |  |
| Reverse transfer capacitance | C <sub>rss</sub>       | f = 1MHz                           | -      | 70   | -    |       |  |
| Turn - on delay time         | t <sub>d(on)</sub> *4  | $V_{DD} \simeq 15V, V_{GS} = 4.5V$ | -      | 10   | 1    |       |  |
| Rise time                    | t <sub>r</sub> *4      | I <sub>D</sub> = 2.0A              | -      | 18   | -    | no    |  |
| Turn - off delay time        | t <sub>d(off)</sub> *4 | $R_L \simeq 7.5\Omega$             | -      | 37   | 1    | ns    |  |
| Fall time                    | t <sub>f</sub> *4      | $R_G = 10\Omega$                   | -      | 19   | 1    |       |  |

## • Gate charge characteristics $(T_a = 25^{\circ}C)$

|                      | \ u                  | ,  |        |      |      |       |
|----------------------|----------------------|--|--------|------|------|-------|
| Downwater            | arameter Symbol Cond | Conditions                                       | Values |      |      | Unit  |
| Farameter            |                      | Conditions                                       | Min.   | Тур. | Max. | Offic |
| Total gate charge    | Qg*4                 | V <sub>DD</sub> ≃ 15V,                           | -      | 5.9  | 8.3  |       |
| Gate - Source charge | Q <sub>gs</sub> *4   | I <sub>D</sub> = 4.0A,<br>V <sub>GS</sub> = 4.5V | -      | 1.0  | -    | nC    |
| Gate - Drain charge  | Q <sub>gd</sub> *4   | $V_{GS} = 4.5V$                                  | -      | 2.0  | -    |       |

## ●Body diode electrical characteristics (Source-Drain) (T<sub>a</sub> = 25°C)

| Darameter                  | Symbol                    | Conditions                                  | Values |      |      | Unit  |  |
|----------------------------|---------------------------|---|--------|------|------|-------|--|
| Parameter                  | rameter Symbol Conditions |   | Min.   | Тур. | Max. | Offit |  |
| Continuous forward current | I <sub>S</sub>            | T - 25°C                                    | -      | -    | 0.8  | Α     |  |
| Pulse forward current      | I <sub>SP</sub> *1        | T <sub>a</sub> = 25°C                       | -      | -    | 16   | Α     |  |
| Forward voltage            | V <sub>SD</sub> *4        | V <sub>GS</sub> = 0V, I <sub>S</sub> = 0.8A | -      | -    | 1.2  | V     |  |

#### • Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

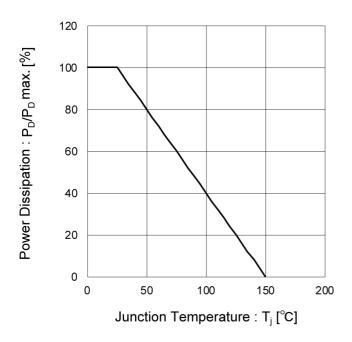
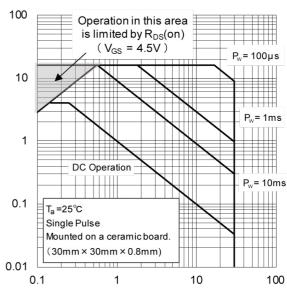


Fig.2 Maximum Safe Operating Area



Drain Current : I<sub>D</sub> [A]

Drain - Source Voltage: V<sub>DS</sub> [V]

Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

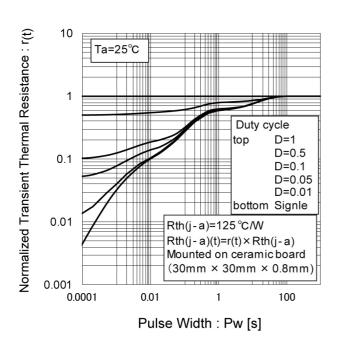
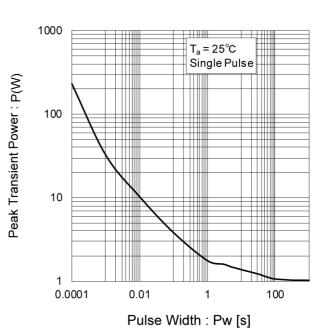


Fig.4 Single Pulse Maximum Power dissipation



#### Electrical characteristic curves

Fig.5 Typical Output Characteristics(I)

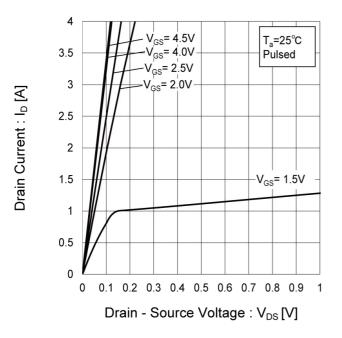


Fig.6 Typical Output Characteristics(II)

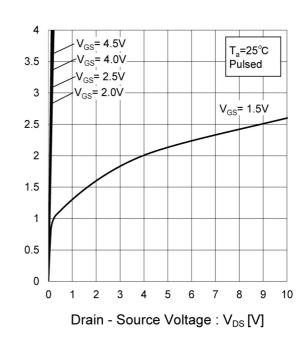
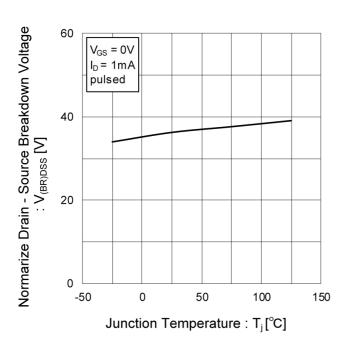


Fig.7 Breakdown Voltage vs. Junction Temperature



Ta= 75°C Ta= 25°C

Drain Current : I<sub>D</sub> [A]

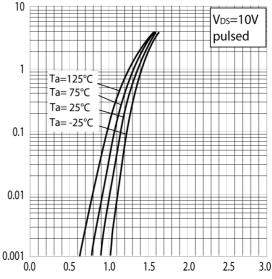


Fig.8 Typical Transfer Characteristics

Gate - Source Voltage : V<sub>GS</sub> [V]

Drain Current : I<sub>D</sub> [A]

Gate Threshold Voltage: V<sub>GS(th)</sub> [V]

#### • Electrical characteristic curves

Fig.9 Gate Threshold Voltage vs. Junction Temperature

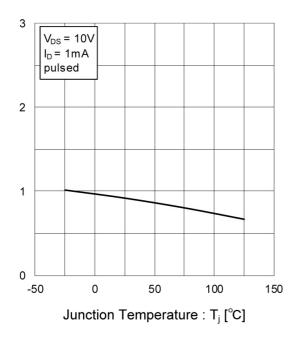


Fig.10 Forward Transfer Admittance vs. Drain Current

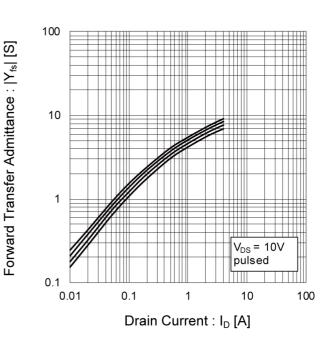


Fig.11 Drain Current Derating Curve

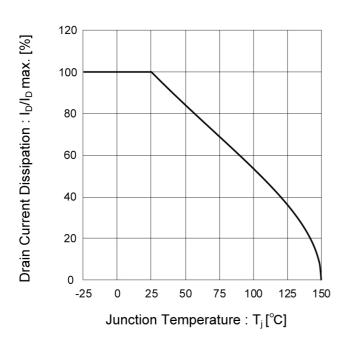
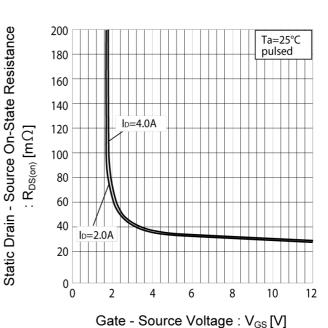


Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage



RTR040N03

#### • Electrical characteristic curves

Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature

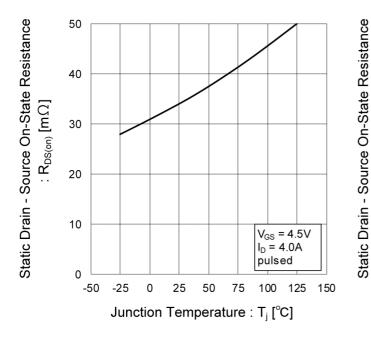
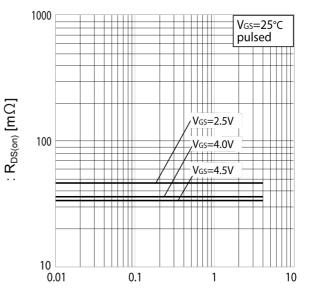


Fig.14 Static Drain - Source On - State Resistance vs. Drain Current(I)



#### • Electrical characteristic curves

Fig.15 Static Drain - Source On - State Resistance vs. Drain Current(II)

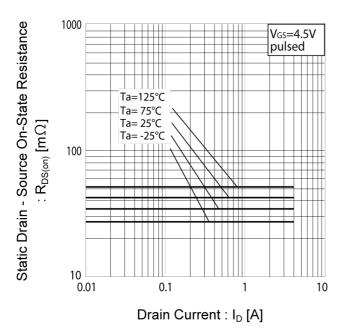


Fig.16 Static Drain - Source On - State Resistance vs. Drain Current(III)

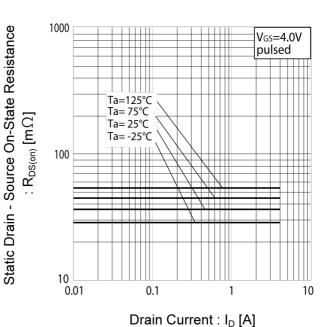
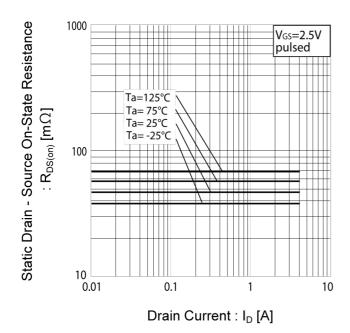


Fig.17 Static Drain - Source On - State Resistance vs. Drain Current(IV)



8/11

#### • Electrical characteristic curves

Fig.18 Typical Capacitance vs. Drain - Source Voltage

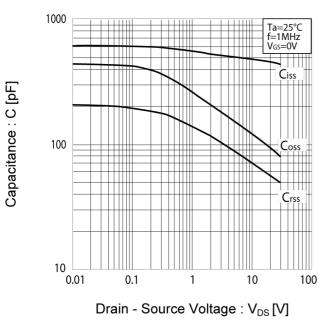
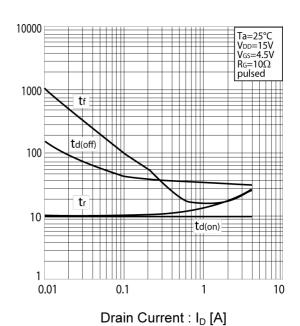


Fig.19 Switching Characteristics



Switching Time : t [ns]

Fig.20 Dynamic Input Characteristics

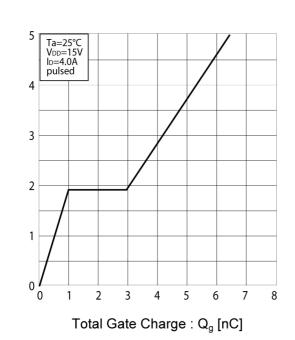
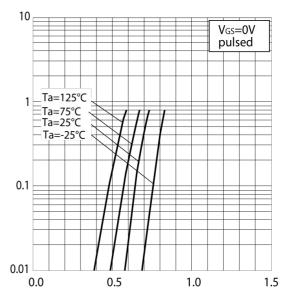


Fig.21 Source Current vs. Source Drain Voltage



Source - Drain Voltage: V<sub>SD</sub> [V]

Gate - Source Voltage :  $V_{GS}$  [V]

Source Current : I<sub>s</sub> [A]

#### Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

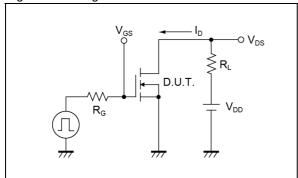


Fig.2-1 Gate Charge Measurement Circuit

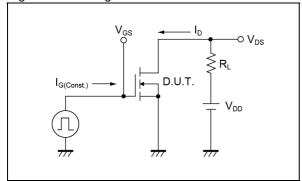


Fig.1-2 Switching Waveforms

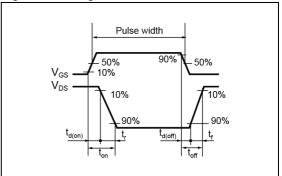
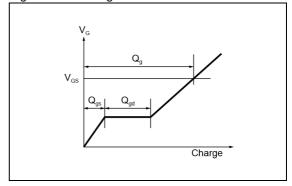
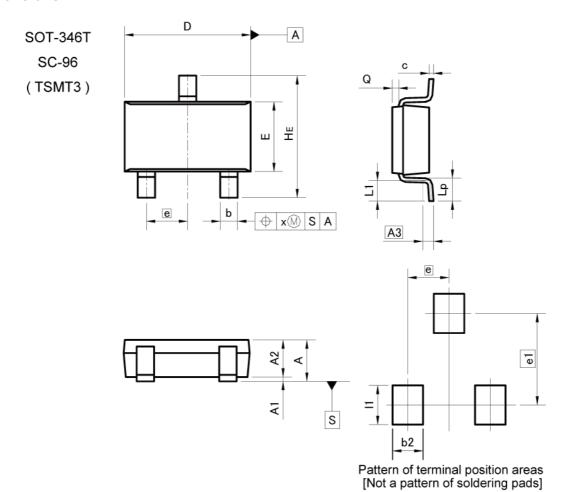


Fig.2-2 Gate Charge Waveform



#### Dimensions



| DIM | MILIM           | ETERS | INC             | HES   |
|-----|-----------------|-------|-----------------|-------|
| DIM | MIN             | MAX   | MIN             | MAX   |
| Α   | -               | 1.00  | -               | 0.039 |
| A1  | 0.00            | 0.10  | 0.000           | 0.004 |
| A2  | 0.75            | 0.95  | 0.030           | 0.037 |
| A3  | 0.3             | 25    | 0.0             | 10    |
| b   | 0.35            | 0.50  | 0.014           | 0.020 |
| С   | 0.10            | 0.26  | 0.004           | 0.010 |
| D   | 2.80            | 3.00  | 0.110           | 0.118 |
| E   | 1.50            | 1.80  | 0.059           | 0.071 |
| е   | 0.9             | 95    | 0.0             | 37    |
| HE  | 2.60            | 3.00  | 0.102           | 0.118 |
| L1  | 0.30            | 0.60  | 0.012           | 0.024 |
| Lp  | 0.40            | 0.70  | 0.016           | 0.028 |
| Q   | 0.05            | 0.25  | 0.002           | 0.010 |
| Х   | <del>-</del> -2 | 0.20  | <del>-</del> -3 | 0.008 |

| DIM | MILIMETERS      |      | INCHES      |       |
|-----|-----------------|------|-------------|-------|
| DIM | MIN             | MAX  | MIN         | MAX   |
| b2  |                 | 0.70 | -           | 0.028 |
| e1  | 2.10            |      | 0.0         | 83    |
| l1  | <del>-</del> -2 | 0.90 | <del></del> | 0.035 |

Dimension in mm/inches



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|---------|----------|------------|-----------|
| CLASSⅢ  | CLACCIII | CLASS II b | CI VCCIII |
| CLASSIV | CLASSⅢ   | CLASSⅢ     | CLASSⅢ    |

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  - [h] Use of the Products in places subject to dew condensation
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- 7. De-rate Power Dissipation (Pd) depending on Ambient temperature (Ta). When used in sealed area, confirm the actual ambient temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- 9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

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This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

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